High Voltage, High and Low Side Driver

The NCP5304 is a High Voltage Power gate Driver providing two outputs for direct drive of 2 N-channel power MOSFETs or IGBTs arranged in a half-bridge configuration.

It uses the bootstrap technique to insure a proper drive of the High–side power switch. The driver works with 2 independent inputs with cross conduction protection.

Features

- High Voltage Range: up to 600 V
- dV/dt Immunity ±50 V/nsec
- Negative Current Injection Characterized Over the Temperature Range
- Gate Drive Supply Range from 10 V to 20 V
- High and Low Drive Outputs
- Output Source / Sink Current Capability 250 mA / 500 mA
- 3.3 V and 5 V Input Logic Compatible
- Up to V_{CC} Swing on Input Pins
- Extended Allowable Negative Bridge Pin Voltage Swing to -10 V for Signal Propagation
- Matched Propagation Delays between Both Channels
- Outputs in Phase with the Inputs
- Cross Conduction Protection with 100 ns Internal Fixed Dead Time
- Under V_{CC} LockOut (UVLO) for Both Channels
- Pin-to-Pin Compatible with Industry Standards
- These are Pb–Free Devices

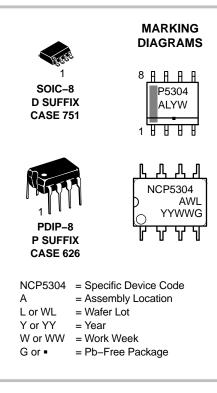
Typical Applications

- Half-bridge Power Converters
- Full-bridge Converters

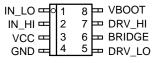


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PINOUT INFORMATION



8 Pin Package

ORDERING INFORMATION

D	evice	Package	Shipping [†]
NCP53	04PG	PDIP-8 (Pb-Free)	50 Units / Rail
NCP53	04DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

⁺For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

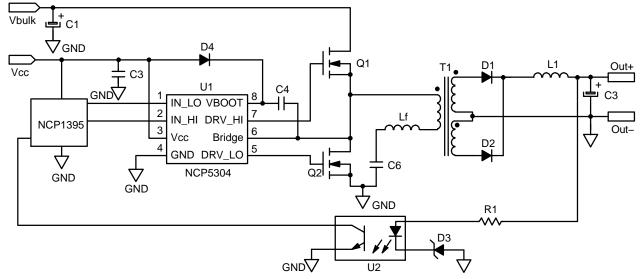


Figure 1. Typical Application Resonant Converter (LLC type)

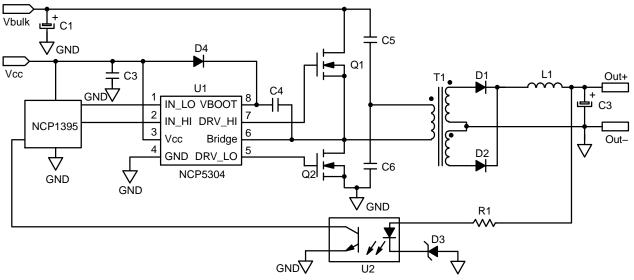


Figure 2. Typical Application Half Bridge Converter

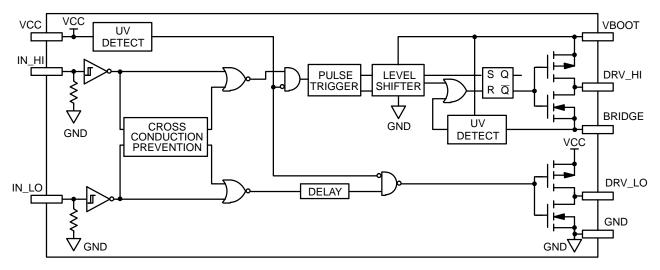


Figure 3. Detailed Block Diagram

PIN DESCRIPTIONS

Pin No.	Pin Name	Pin Function		
1	IN_LO	Logic Input for Low side driver output in phase		
2	IN_HI	ogic Input for High side driver output in phase		
3	VCC	Low side and main power supply		
4	GND	Ground		
5	DRV_LO	Low side gate drive output		
6	BRIDGE	Bootstrap return or High side floating supply return		
7	DRV_HI	High side gate drive output		
8	VBOOT	Bootstrap power supply		

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
V _{CC}	Main power supply voltage	-0.3 to 20	V
V _{CC_transient}	Main transient power supply voltage: IV _{CC_max} = 5 mA during 10 ms	23	V
VBRIDGE	VHV: High Voltage BRIDGE pin	-1 to 600	V
VBRIDGE	Allowable Negative Bridge Pin Voltage for IN_LO Signal Propagation to DRV_LO (see characterization curves for detailed results)	-10	V
V _{BOOT} -V _{BRIDGE}	VHV: Floating supply voltage	-0.3 to 20	V
V _{DRV_HI}	VHV: High side output voltage	V _{BRIDGE} – 0.3 to V _{BOOT} + 0.3	V
V _{DRV_LO}	Low side output voltage	-0.3 to V _{CC} + 0.3	V
dV _{BRIDGE} /dt	Allowable output slew rate	50	V/ns
V _{IN_XX}	Inputs IN_HI, IN_LO	-1.0 to V _{CC} + 0.3	V
	ESD Capability: – HBM model (all pins except pins 6–7–8 in 8 pins package or 11–12–13 in 14 pins package)	2	kV
	 Machine model (all pins except pins 6–7–8 in 8 pins package or 11–12–13 in 14 pins package) 	200	V
	Latch up capability per Jedec JESD78		
$R_{ extsf{ heta}JA}$	Power dissipation and Thermal characteristics PDIP–8: Thermal Resistance, Junction–to–Air SO–8: Thermal Resistance, Junction–to–Air	100 178	°C/W
T _{J_max}	Maximum Operating Junction Temperature	+150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTIC (V _{CC} = V _{boot} = 15 V, V _{GND} = V _{bridg}	$_{qe}$, $-40^{\circ}C < T_{J} < 125^{\circ}C$, Outputs loaded with 1 nF)
--	---

		T _J –40°C to 125°C			
Rating	Symbol	Min	Тур	Max	Units
OUTPUT SECTION	· · · ·				
Output high short circuit pulsed current V _{DRV} = 0 V, PW \leq 10 µs (Note 1)	I _{DRVsource}	-	250	-	mA
Output low short circuit pulsed current V _{DRV} = V _{CC} , PW \leq 10 µs (Note 1)	I _{DRVsink}	_	500	-	mA
Output resistor (Typical value @ 25°C) Source	R _{OH}	_	30	60	Ω
Output resistor (Typical value @ 25°C) Sink	R _{OL}	_	10	20	Ω
High level output voltage, V _{BIAS} –V _{DRV_XX} @ I _{DRV_XX} = 20 mA	V _{DRV_H}	_	0.7	1.6	V
Low level output voltage V _{DRV_XX} @ I _{DRV_XX} = 20 mA	V _{DRV_L}	_	0.2	0.6	V
DYNAMIC OUTPUT SECTION			•	•	
Turn-on propagation delay (Vbridge = 0 V)	t _{ON}	-	100	170	ns
Turn–off propagation delay (Vbridge = 0 V or 50 V) (Note 2)	t _{OFF}	_	100	170	ns
Output voltage rise time (from 10% to 90% @ V _{CC} = 15 V) with 1 nF load	tr	_	85	160	ns
Output voltage fall time (from 90% to 10% $@V_{CC} = 15 \text{ V}$) with 1 nF load	tf	-	35	75	ns
Propagation delay matching between the High side and the Low side @ 25°C (Note 3)	Δt	-	20	35	ns
Internal fixed dead time (Note 4)	DT	65	100	190	ns
Minimum input width that changes the output	t _{PW1}	_	-	50	ns
Maximum input width that does not change the output	t _{PW2}	20	-	-	ns
INPUT SECTION			•	•	
Low level input voltage threshold	V _{IN}	_	-	0.8	V
Input pull–down resistor (V _{IN} < 0.5 V)	R _{IN}	_	200	-	kΩ
High level input voltage threshold	V _{IN}	2.3	-	-	V
Logic "1" input bias current @ V _{IN_XX} = 5 V @ 25°C	I _{IN+}	_	5	25	μΑ
Logic "0" input bias current @ V _{IN_XX} = 0 V @ 25°C	I _{IN}	_	_	2.0	μΑ
SUPPLY SECTION			•	•	
V _{CC} UV Start-up voltage threshold	VCC_stup	8.0	8.9	9.9	V
V _{CC} UV Shut–down voltage threshold	VCC_shtdwn	7.3	8.2	9.1	V
Hysteresis on V _{CC}	VCC_hyst	0.3	0.7	-	V
Vboot Start–up voltage threshold reference to bridge pin (Vboot_stup = Vboot – Vbridge)	Vboot_stup	8.0	8.9	9.9	V
Vboot UV Shut-down voltage threshold	Vboot_shtdwn	7.3	8.2	9.1	V
Hysteresis on Vboot	Vboot_shtdwn	0.3	0.7	-	V
Leakage current on high voltage pins to GND (V _{BOOT} = V _{BRIDGE} = DRV_HI = 600 V)	I _{HV_LEAK}	_	5	40	μΑ
Consumption in active mode (V_{CC} = Vboot, fsw = 100 kHz and 1 nF load on both driver outputs)	ICC1	_	4	5	mA
Consumption in inhibition mode (V _{CC} = Vboot)	ICC2	-	250	400	μΑ
V _{CC} current consumption in inhibition mode	ICC3	-	200	-	μA
Vboot current consumption in inhibition mode	ICC4	_	50	_	μΑ

Parameter guaranteed by design
 Turn-off propagation delay @ Vbridge = 600 V is guaranteed by design
 See characterization curve for ∆t parameters variation on the full range temperature.
 Timing diagram definition see Figure 7.
 Timing diagram definition see Figure 5 and Figure 6.
 Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

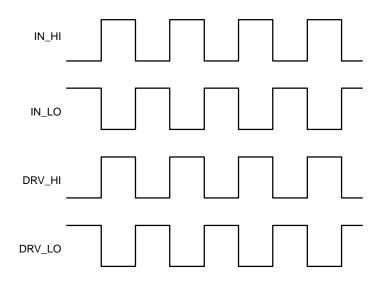


Figure 4. Input/Output Timing Diagram

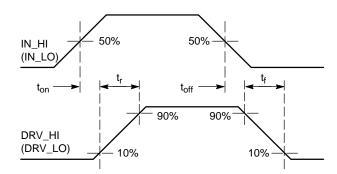
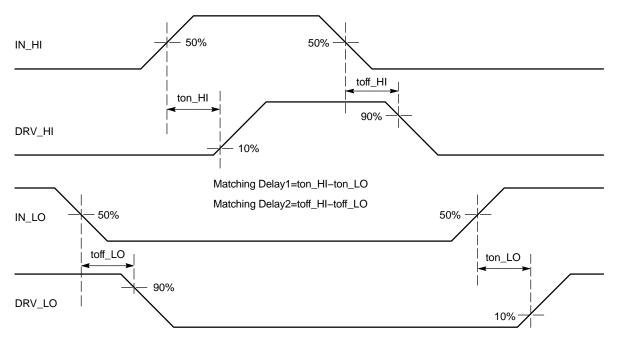


Figure 5. Propagation Delay and Rise / Fall Time Definition





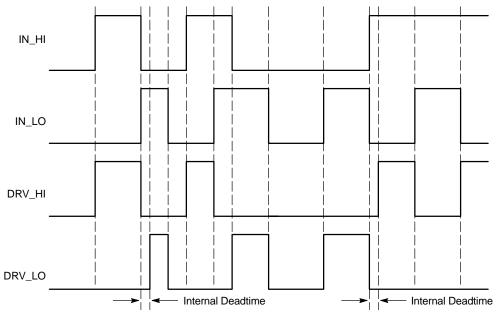
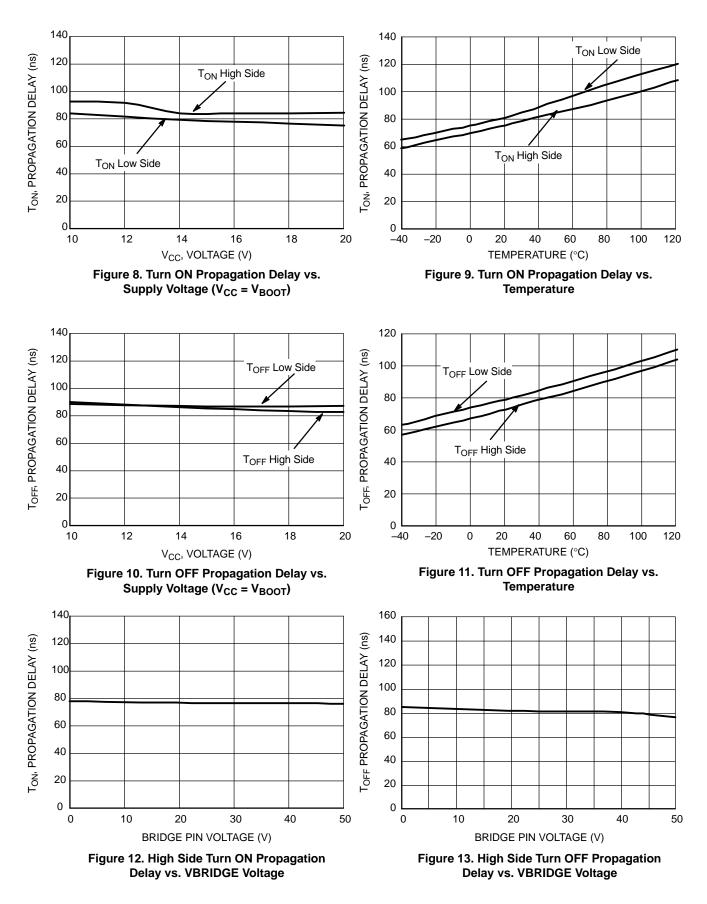
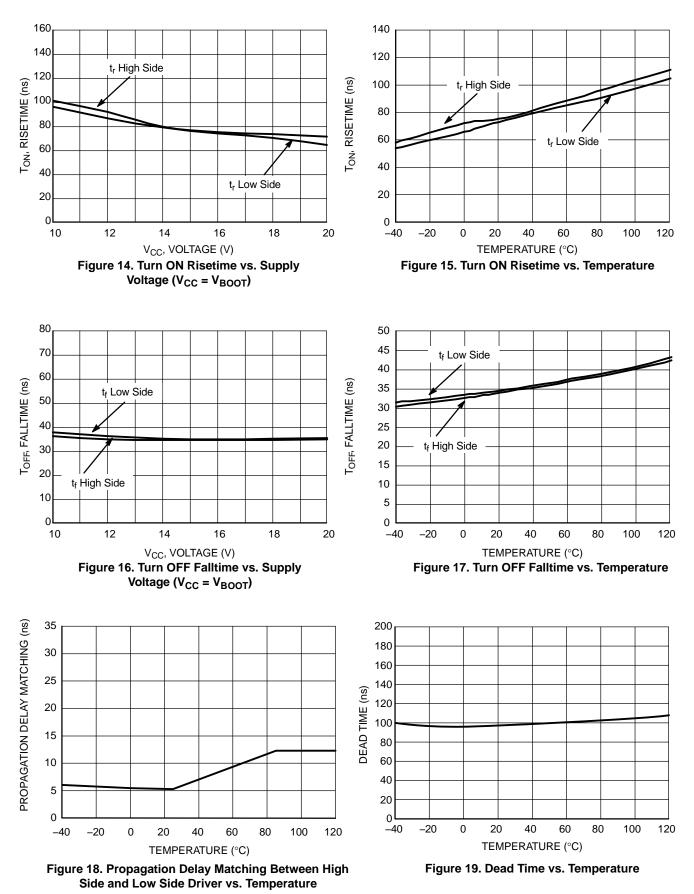
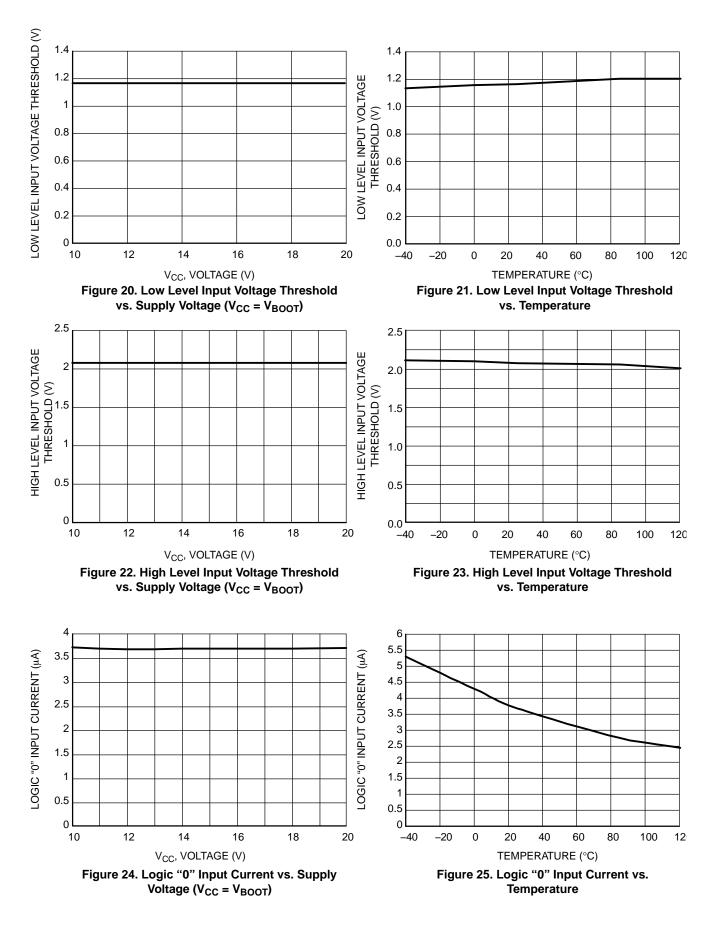


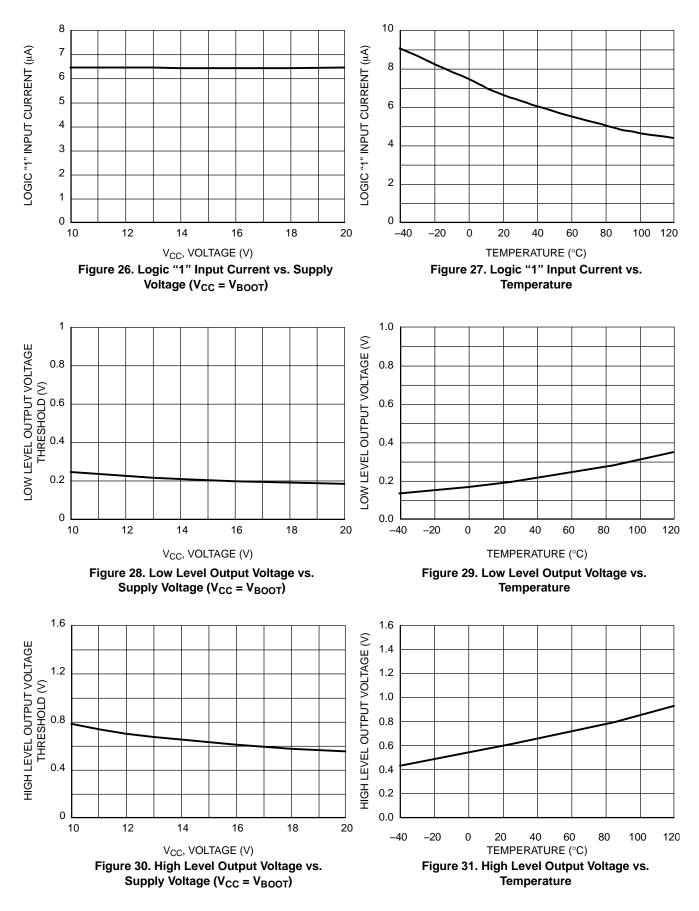
Figure 7. Input/Output Cross Conduction Output Protection Timing Diagram

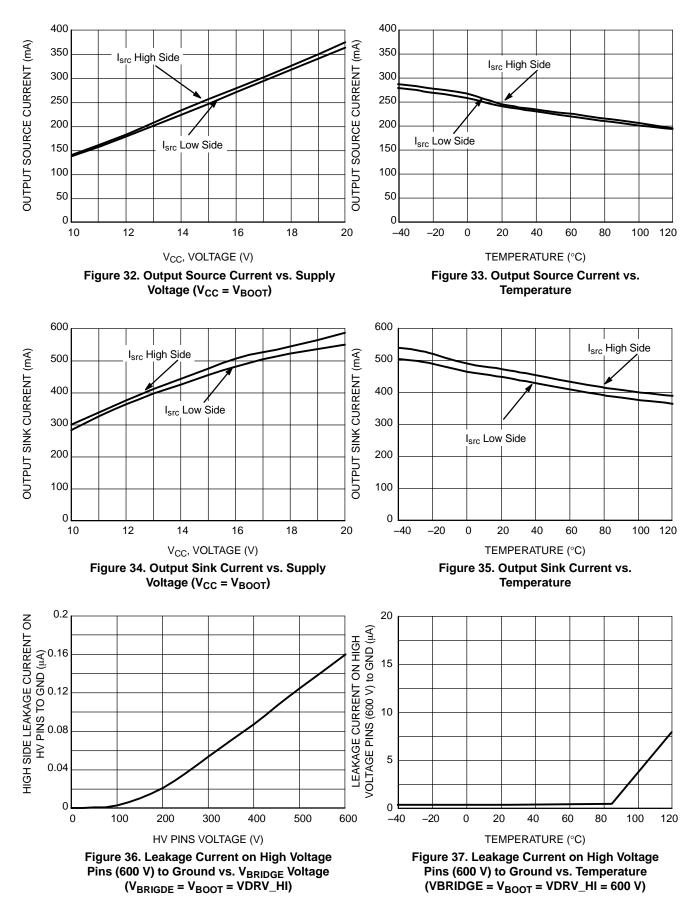
CHARACTERIZATION CURVES

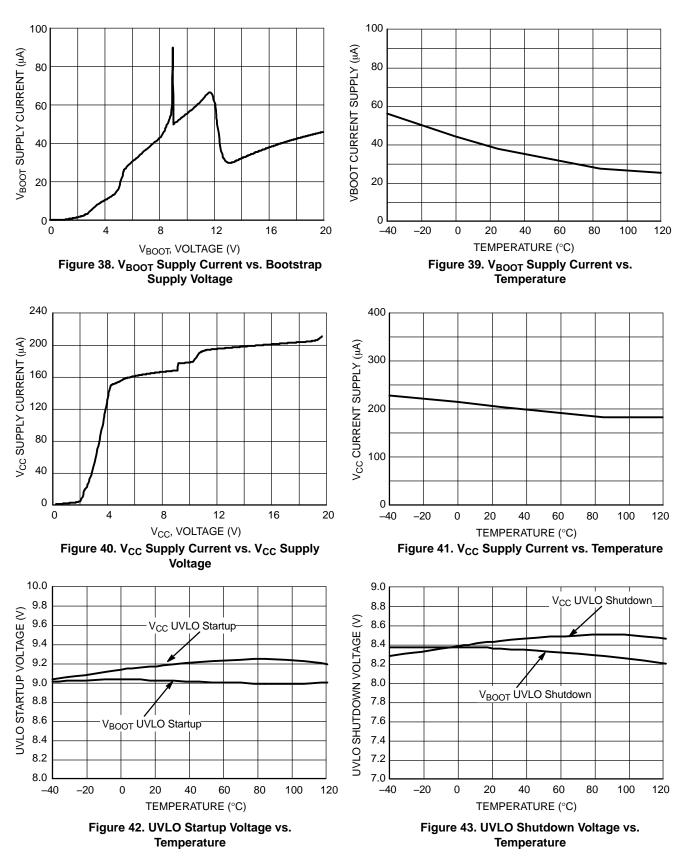


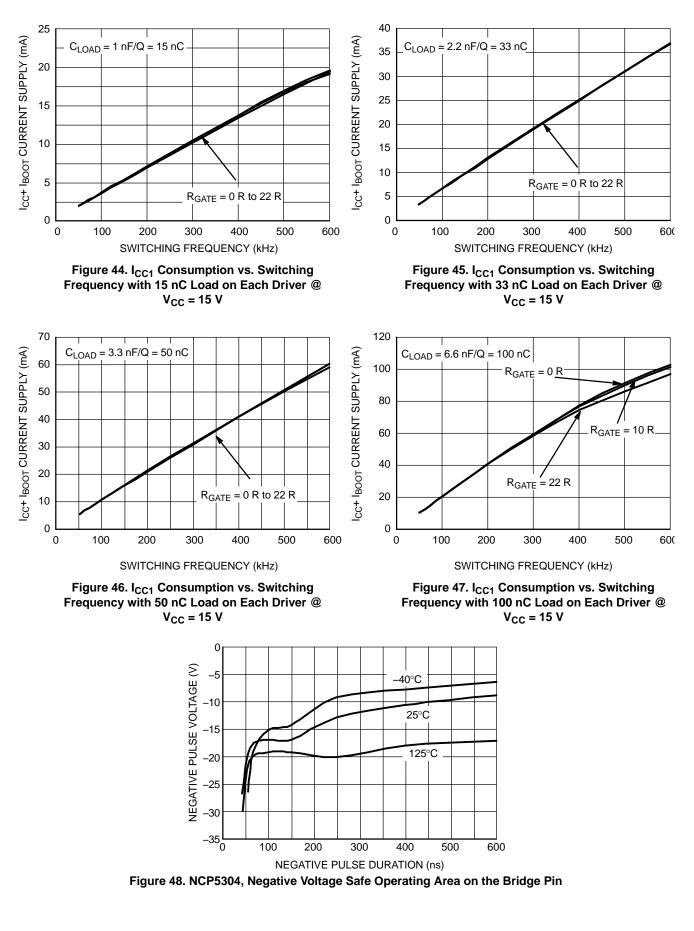












APPLICATION INFORMATION

Negative Voltage Safe Operating Area

When the driver is used in a half bridge configuration, it is possible to see negative voltage appearing on the bridge pin (pin 6) during the power MOSFETs transitions. When the high-side MOSFET is switched off, the body diode of the low-side MOSFET starts to conduct. The negative voltage applied to the bridge pin thus corresponds to the forward voltage of the body diode. However, as pcb copper tracks and wire bonding introduce stray elements (inductance and capacitor), the maximum negative voltage of the bridge pin will combine the forward voltage and the oscillations created by the parasitic elements. As any CMOS device, the deep negative voltage of a selected pin can inject carriers into the substrate, leading to an erratic behavior of the concerned component. ON Semiconductor provides characterization data of its half-bridge driver to show the maximum negative voltage the driver can safely operate with. To prevent the negative injection, it is the designer duty to verify that the amount of negative voltage pertinent to his/her application does not exceed the characterization curve we provide, including some safety margin.

In order to estimate the maximum negative voltage accepted by the driver, this parameter has been characterized over full the temperature range of the component. A test fixture has been developed in which we purposely negatively bias the bridge pin during the freewheel period of a buck converter. When the upper gate voltage shows signs of an erratic behavior, we consider the limit has been reached.

Figure 48, illustrates the negative voltage safe operating area. Its interpretation is as follows: assume a negative 10 V pulse featuring a 100 ns width is applied on the bridge pin, the driver will work correctly over the whole die temperature range. Should the pulse swing to -20 V, keeping the same width of 100 ns, the driver will not work properly or will be damaged for temperatures below 125° C.

Summary:

- If the negative pulse characteristic (negative voltage level & pulse width) is above the curves the driver runs in safe operating area.
- If the negative pulse characteristic (negative voltage level and pulse width) is below one or all curves the driver will NOT run in safe operating area.

Note, each curve of the Figure 48 represents the negative voltage and width level where the driver starts to fail at the corresponding die temperature.

If in the application the bridge pin is too close of the safe operating limit, it is possible to limit the negative voltage to the bridge pin by inserting one resistor and one diode as follows:

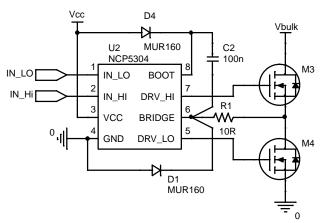
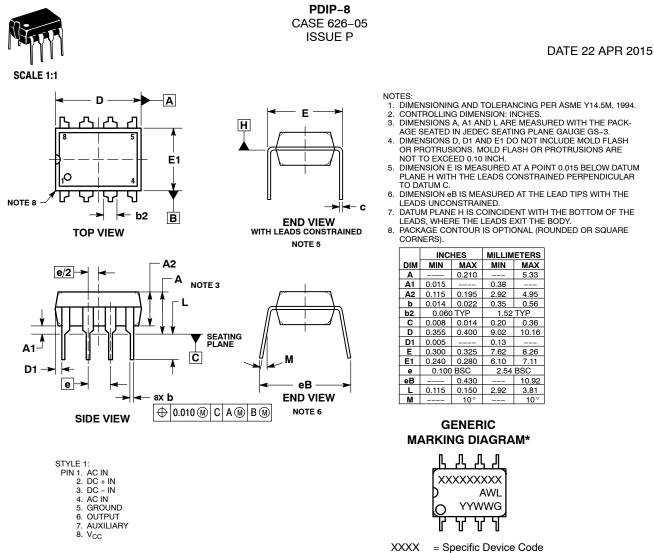


Figure 49. R1 and D1 Improves the Robustness of the Driver

R1 and D1 should be placed as close as possible of the driver. D1 should be connected directly between the bridge pin (pin 6) and the ground pin (pin 4). By this way the negative voltage applied to the bridge pin will be limited by D1 and R1 and will prevent any wrong behavior.





A = Assembly Location

- WL = Wafer Lot
- YY = Year
- WW = Work Week
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ■", may or may not be present.







*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR З. 4. EMITTER EMITTER 5. 6. BASE 7 BASE 8. EMITTER STYLE 5: PIN 1. DRAIN 2. DRAIN З. DRAIN DRAIN 4. 5. GATE 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6. BASE, DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. 4. TXE 5. RXE 6. VFF GND 7. 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 З. CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C З. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. EMITTER, #1 BASE, #2 2. З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

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STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1
STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd
STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 7. DRAIN 1 8. DRAIN 1
STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON
STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1
STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT
STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN

DATE 16 FEB 2011

STYLE 4: ANODE ANODE PIN 1. 2. ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE, #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE SOURCE 2. 3. 4. GATE 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER З. COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE CATHODE COLLECTOR/ANODE 6. 7. COLLECTOR/ANODE 8. STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET 3. 4. GND 5. 6. V MON VBULK 7. VBULK 8. VIN

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8. GATE 1

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8

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COLLECTOR, #1

COLLECTOR, #1

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 00-9091-LRPP
 00-9291-RDPP
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 6131-218-17149P

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